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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No. 10/041,896
 Filing Date January 7, 2002
 Inventorship Brenda D. Kraus et al.
 Assignee Micron Technology, Inc.
 Group Art Unit 2813
 Examiner Yennhu B. Huynh
 Attorney's Docket No. MI22-1859
 Customer No. 021567
 Title: DRAM Circuitry Having Storage Capacitors Which Include Capacitor
 Dielectric Regions Comprising Aluminum Nitride

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. Copies of the cited art are attached hereto. No admission is made regarding whether all the submitted references are prior art.

This Supplemental Information Disclosure Statement is being filed before the mailing of a first office action after the filing of a request for continued examination. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 11-20-03

By: [Signature]
 Mark S. Matkin
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